

AMENDMENTS TO THE CLAIMS

1. (Currently amended) The semiconductor device according to claim ~~30~~ 30, wherein ~~one or more wiring trenches are formed in each of said plurality of wiring insulating films along a periphery of said semiconductor chip in such a manner as to surround said~~ specified region comprises a circuit formation portion, as said specified region,

~~wherein in each of said one or more wiring trenches, a conductive layer made up of copper or a copper-based conductive material is buried via a first copper diffusion preventing film, in such a manner that the respective wiring trenches corresponding to each other in said plurality of wiring insulating films are connected with each other upwardly or downwardly, and~~

~~wherein a second copper diffusion preventing film is formed between each of said plurality of wiring insulating films and an other one of said plurality of wiring insulating films being adjacent thereto upwardly or downwardly, in such a manner as to be connected with the corresponding first copper diffusion preventing film.~~

2. (Previously presented) The semiconductor device according to claim 30, wherein said at least one conductive layer is connected to a diffusion region formed in said semiconductor substrate.

3. (Canceled)

4. (Currently amended) The semiconductor device according to claim ~~34~~ 36:

wherein at least one seal ring made of a conductive material is formed along a periphery of said semiconductor chip so as to surround said circuit formation portion as said

specified region, said at least one seal ring being connected with said semiconductor substrate and being buried in said plurality of wiring insulating films in such a manner as to extend over said wiring insulating films.

5. (Currently amended) The semiconductor device according to claim-~~34~~ 36:
wherein one or more slit-like notches are formed at specified positions in said seal rings in such a manner that the respective slit-like notches in two seal rings ~~being that are~~ adjacent to each other are not aligned.
6. (Currently amended) The semiconductor device according to claim-~~34~~ 36, wherein, said at least one seal ring comprises a damascene wiring structure, ~~as well as said multi-layer interconnection of said circuit formation portion.~~
7. (Original) The semiconductor device according to claim 6, wherein said damascene wiring structure comprises a single damascene wiring structure.
8. (Original) The semiconductor device according to claim 6, wherein said damascene wiring structure comprises a dual damascene wiring structure.
9. (Original) The semiconductor device according to claim 6, wherein said damascene wiring structure comprises a combination of a single damascene wiring structure and a dual damascene wiring structure.
10. (Currently amended) The semiconductor device according to claim-~~34~~ 36, wherein

said at least one seal ring is connected to a diffusion region formed in said semiconductor substrate.

11. (Currently amended) The semiconductor device according to claim-~~34~~ 36, wherein:
_____ said at least one seal ring is connected via a contact to a diffusion region formed in said semiconductor substrate, and
_____ said contact and said diffusion region ~~being~~ are formed so as to match approximately said at least one seal ring in shape.

12. (Currently amended) The semiconductor device according to claim-~~34~~ 36, wherein:
_____ said at least one seal ring is connected via a contact to a diffusion region formed in said semiconductor substrate, and
_____ said contact and said diffusion region ~~being~~ are formed without matching said at least one seal ring.

13. (Currently amended) The semiconductor device according to claim-~~34~~ 36, wherein said at least one ~~seal ring~~ conductive layer comprises copper or a copper-based conductive material.

14-21. (Canceled)

22. (Currently amended) The semiconductor device according to claim-~~34~~ 36:
wherein an assembly pad, a characteristics evaluation pad, or a screening evaluation pad is formed on a surface of said semiconductor substrate in such a manner to be electrically

connected to said circuit formation portion, and

wherein at least one seal ring made of a conductive material is formed in such a manner as to surround said assembly pad, said characteristics evaluation pad, or said screening evaluation pad as said specified region, said at least one seal ring being connected with said semiconductor substrate and extending over said wiring insulating films.

23. (Original) The semiconductor device according to claim 22, wherein, at least one bottomed seal ring, being not connected with said semiconductor substrate, is formed in such a manner as to surround said assembly pad, said characteristics evaluation pad, or said screening evaluation pad.

24. (Original) The semiconductor device according to claim 22, wherein said at least one seal ring comprises a damascene wiring structure.

25. (Original) The semiconductor device according to claim 23, wherein said at least one bottomed seal ring comprising a damascene wiring structure.

26. (Currently amended) The semiconductor device according to claim ~~34~~ 36:

wherein a plurality of fuse elements for each replacing a defective circuit element therewith is provided on a surface of said semiconductor substrate in such a manner as to be electrically connected with said circuit formation portion, and

wherein at least one seal ring each made of a conductive layer is formed in such a manner as to surround said plurality of fuse elements as said specified region, said at least one seal ring being connected with said semiconductor substrate and extending over said plurality

of wiring insulating films.

27. (Original) The semiconductor device according to claim 26, wherein, at least one bottomed seal ring, being not connected with said semiconductor substrate, is formed in such a manner as to surround said plurality of fuse elements

28. (Original) The semiconductor device according to claim 26, wherein said at least one seal ring comprises a damascene wiring structure.

29. (Original) The semiconductor device according to claim 27, wherein said at least one bottomed seal ring comprises a damascene wiring structure.

30. (Currently amended) A semiconductor device comprising:

a semiconductor chip provided with a circuit formation portion comprising a plurality of wiring insulating films stacked on top of each other in layers on a semiconductor substrate, and a multi-layer interconnection formed in said plurality of wiring insulating films,

wherein one or more wiring trenches are formed in each of said plurality of wiring insulating films along a periphery of said semiconductor chip in such a manner as to surround a specified region on said semiconductor substrate,

wherein in each of said one or more wiring trenches, a conductive layer ~~made up of copper or a copper-based conductive material~~ is buried via a first ~~copper~~ conductive layer diffusion preventing film, in such a manner that the respective wiring trenches corresponding to each other in said plurality of wiring insulating films are connected with each other upwardly or downwardly, and

wherein each wiring insulation film comprises a dielectric constant film, and a second copper-conductive layer diffusion preventing film is formed between each of said plurality of wiring insulating films and another one of said plurality of wiring insulating films being adjacent thereto upwardly or downwardly, in such a manner as to be connected with the a corresponding one of said first copper-conductive layer diffusion preventing film films; and
wherein at least one of said wiring insulation films comprises a low-dielectric constant film comprising methyl-silsesquioxane or hydrogen-silsesquioxane.

31. (Currently amended) The semiconductor device according to claim-301,
wherein an assembly pad, a characteristics evaluation pad, or a screening evaluation pad is formed on a surface of said semiconductor substrate in such a manner to be electrically connected to said circuit formation portion, and

wherein said one or more wiring trenches ~~are formed in each of said plurality of wiring insulating films along a periphery of said semiconductor chip in such a manner as to surround said assembly pad, said characteristics evaluation pad, or said screening evaluation pad as said specified region.~~

32. (Currently amended) The semiconductor device according to claim-301,
wherein a plurality of fuse elements, each adapted for ~~each~~-replacing a defective circuit element, ~~therewith is~~ are provided on a surface of said semiconductor substrate in such a manner as to be electrically connected with said circuit formation portion, and

wherein said one or more wiring trenches ~~are formed in each of said plurality of wiring insulating films along a periphery of said semiconductor chip in such a manner as to surround said plurality of fuse elements as said specified region.~~

33. (Previously presented) The semiconductor device according to claim 30,
wherein a plurality of wiring trenches are formed, with a conductive layer in each, and
wherein one or more slit-like notches are formed at specified positions in said
conductive ~~layer~~ layers in such a manner that the respective slit-like notches in two of said
conductive layers ~~being that are~~ adjacent to each other are not aligned.

34. (Canceled)

35. (New) The semiconductor device according to claim 2, wherein said diffusion region
comprises an N-type diffusion region.

36. (New) The semiconductor device according to claim 30, wherein said conductive
layers in said one or more wiring trenches comprise seal rings.

37. (New) a semiconductor device, comprising:
a semiconductor chip provided with a circuit formation portion comprising a plurality
of wiring insulating films stacked on top of each other in layers on a semiconductor substrate,
and a multi-layer interconnection formed in said plurality of wiring insulating films,

wherein one or more wiring trenches are formed in each of said plurality of wiring
insulating films along a periphery of said semiconductor chip in such a manner as to surround
a specified region on said semiconductor substrate,

wherein in each wiring trench, a conductive layer is buried via a first conductive layer
diffusion preventing film, in such a manner that the respective wiring trenches corresponding
to each other in said plurality of wiring insulating films are connected with each other

upwardly or downwardly,

wherein each wiring insulating film comprises a dielectric constant film, and a second conductive layer diffusion preventing film connected with a corresponding one of said first conductive layer diffusion preventing films, and

wherein at least one wiring insulating film comprises a low-dielectric constant film having a dielectric constant lower than or equal to that of methyl-silsesquioxane.

38. (New) a semiconductor device, comprising:

a semiconductor chip provided with a circuit formation portion comprising a plurality of wiring insulating films stacked on top of each other in layers on a semiconductor substrate, and a multi-layer interconnection formed in said plurality of wiring insulating films,

wherein one or more wiring trenches are formed in each of said plurality of wiring insulating films along a periphery of said semiconductor chip in such a manner as to surround a specified region on said semiconductor substrate,

wherein in each wiring trench, a conductive layer is buried via a first conductive layer diffusion preventing film, in such a manner that the respective wiring trenches corresponding to each other in said plurality of wiring insulating films are connected with each other upwardly or downwardly,

wherein each wiring insulating film comprises a dielectric constant film, and a second conductive layer diffusion preventing film connected with a corresponding one of said first conductive layer diffusion preventing films, and

wherein at least one wiring insulating film comprises a low-dielectric constant film having a dielectric constant lower than or equal to that of hydrogen-silsesquioxane.